

## Features

- N-Channel MOSFET and NPN Transistor in One Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 2)**
- **ESD Protected MOSFET Gate up to 2kV**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 Lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.006 grams (approximate)



## Maximum Ratings – MOSFET, Q1 @<sub>TA</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 1)	$I_D$	160	mA
Pulsed Drain Current (Note 1)	$I_{DM}$	560	mA

## Maximum Ratings - NPN Transistor, Q2 @<sub>TA</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	100	mA

## Thermal Characteristics, Total Device @<sub>TA</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	250	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead. Halogen and Antimony Free.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).

**Electrical Characteristics - MOSFET** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 2)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1.0 5.0	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 2)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.7	0.8	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.1	4	Ω	V <sub>GS</sub> = 4V, I <sub>D</sub> = 100mA
		—	4	5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 80mA
Forward Transconductance	g <sub>FS</sub>	180	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA, f = 1.0KHz
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	25	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.1	—	pF	

**Electrical Characteristics - NPN Transistor** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 4)	V <sub>(BR)CBO</sub>	50	—	—	V	I <sub>C</sub> = 10μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage (Note 4)	V <sub>(BR)CEO</sub>	45	—	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage (Note 4)	V <sub>(BR)EBO</sub>	6	—	—	V	I <sub>E</sub> = 1μA, I <sub>C</sub> = 0
DC Current Gain (Note 4)	h <sub>FE</sub>	200	290	450	—	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA
Collector-Emitter Saturation Voltage (Note 4)	V <sub>CE(SAT)</sub>	—	—	100 300	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage (Note 4)	V <sub>BE(SAT)</sub>	—	700 900	—	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage (Note 4)	V <sub>BE</sub>	580 —	660 —	700 770	mV	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA
Collector Cut-Off Current (Note 4)	I <sub>CBO</sub>	—	—	15 5.0	nA μA	V <sub>CB</sub> = 30V V <sub>CB</sub> = 30V, T <sub>A</sub> = 150°C
Collector-Emitter Cut-Off Current (Note 4)	I <sub>CES</sub>	—	—	100	nA	V <sub>CE</sub> = 45V
Gain Bandwidth Product	f <sub>T</sub>	100	—	—	MHz	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA, f = 100MHz
Output Capacitance	C <sub>OBO</sub>	—	—	4.5	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Noise Figure	NF	—	—	10	dB	V <sub>CE</sub> = 5V, R <sub>S</sub> = 2.0kΩ, f = 1.0kHz, BW = 200Hz

Notes: 4. Short duration pulse test used to minimize self-heating effect.

**MOSFET**

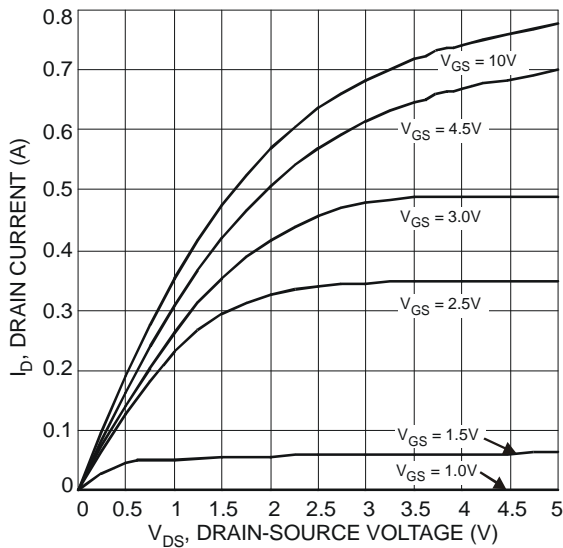


Fig. 1 Typical Output Characteristics

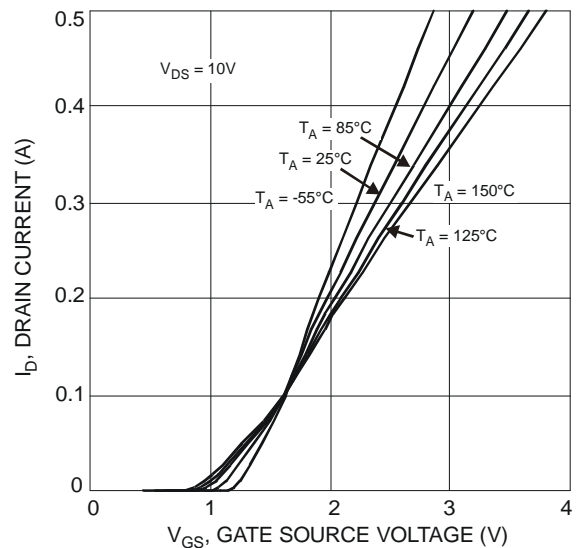


Fig. 2 Typical Transfer Characteristics

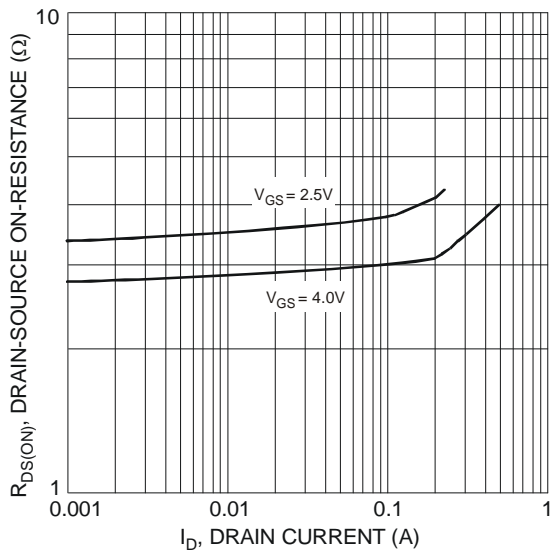


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

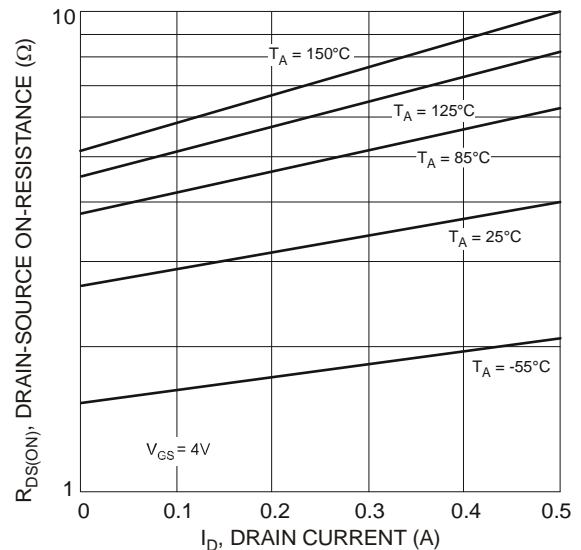


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

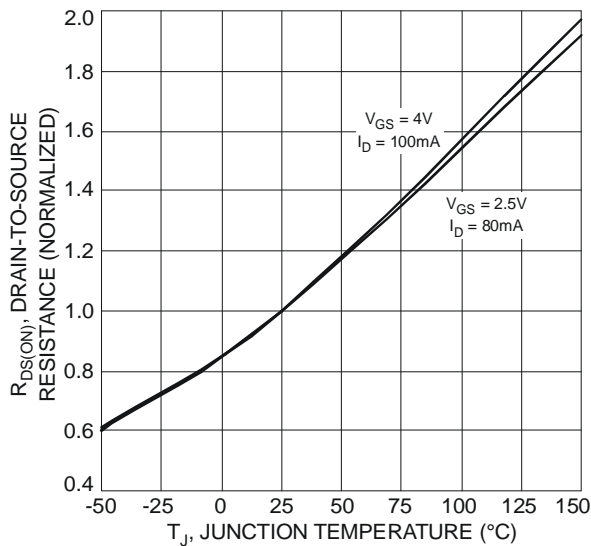


Fig. 5 On-Resistance Variation with Temperature

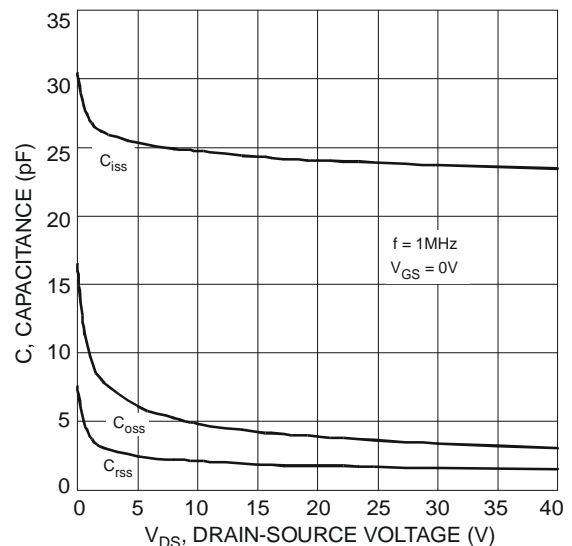


Fig. 6 Typical Capacitance

**MOSFET (continued)**

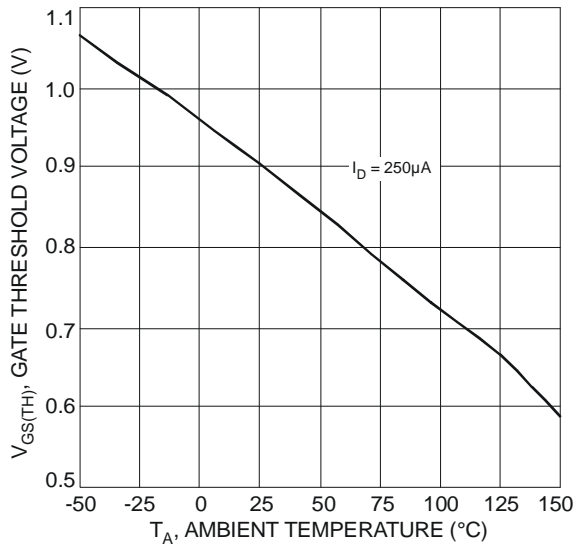


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

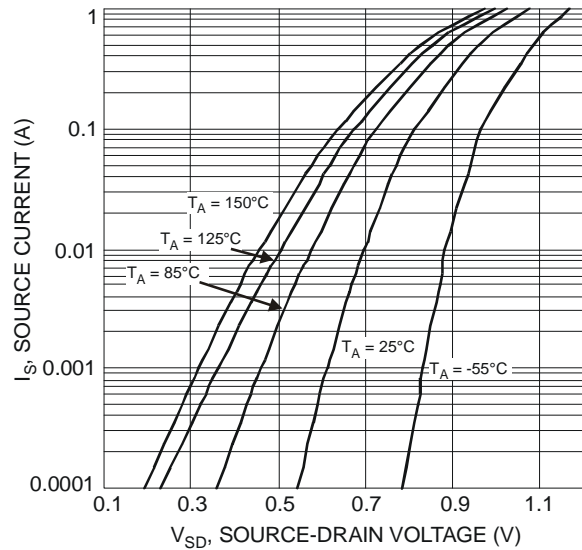


Fig. 8 Diode Forward Voltage vs. Current

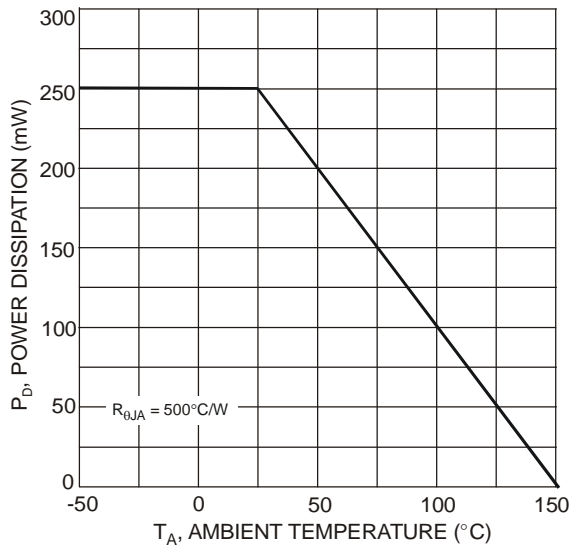


Fig. 9 Derating Curve - Total Package Power Dissipation

**NPN Transistor**

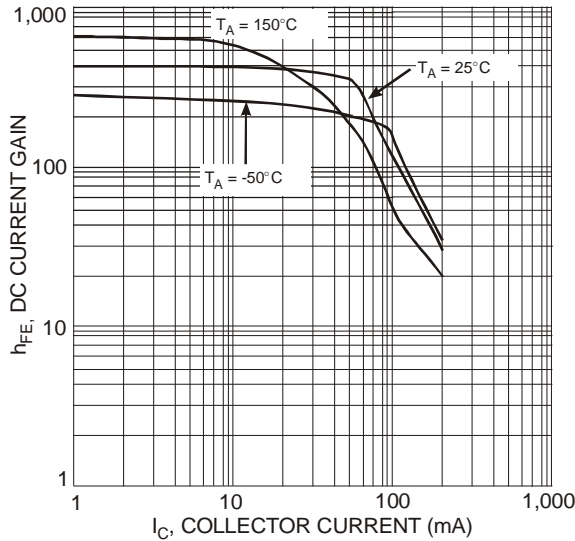


Fig. 10 Typical DC Current Gain vs. Collector Current

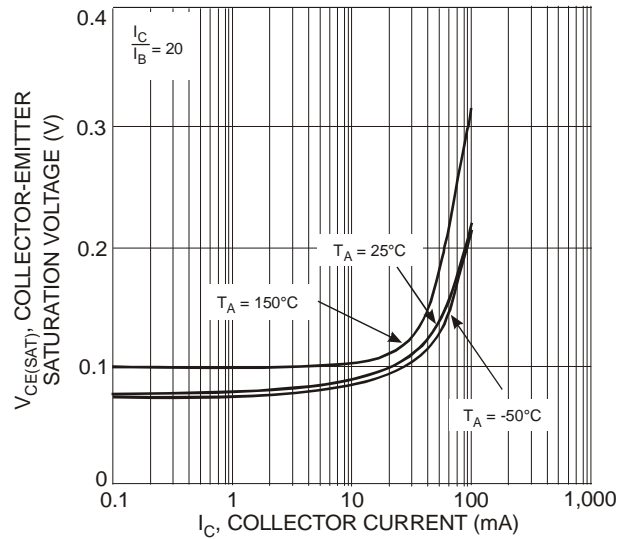


Fig. 11 Typical Collector-Emitter Saturation Voltage vs. Collector Current

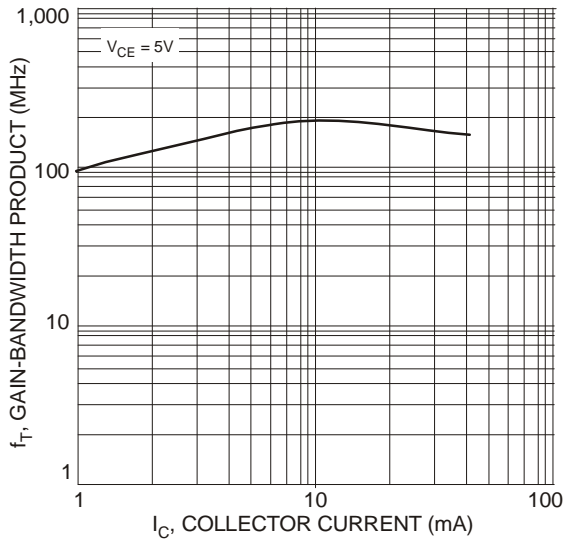


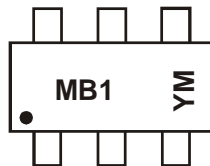
Fig. 12 Typical Gain-Bandwidth Product vs. Collector Current

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMB53D0UDW-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



MB1 = Marking Code  
YM = Date Code Marking  
Y = Year (ex: V = 2008)  
M = Month (ex: 9 = September)

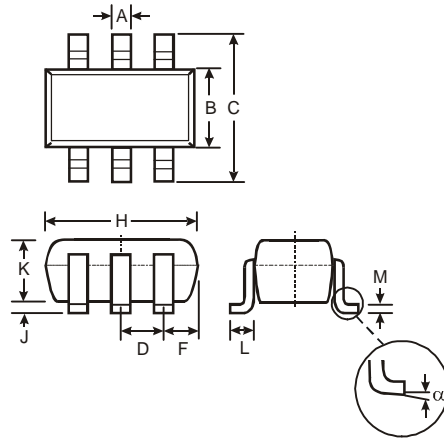
Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

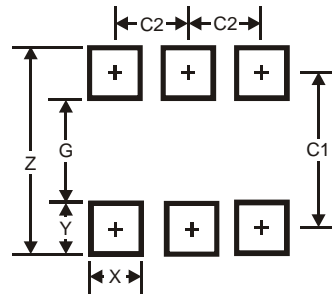
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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